



**MOTOROLA**

**MCM68A316E**

### 2048 X 8 BIT READ ONLY MEMORY

The MCM68A316E is a mask-programmable byte-organized memory designed for use in bus-organized systems. It is fabricated with N-channel silicon-gate technology. For ease of use, the device operates from a single power supply, has compatibility with TTL and DTL, and needs no clocks or refreshing because of static operation.

The memory is compatible with the M6800 Microcomputer Family, providing read only storage in byte increments. Memory expansion is provided through multiple Chip Select inputs. The active level of the Chip Select inputs and the memory content are defined by the user.

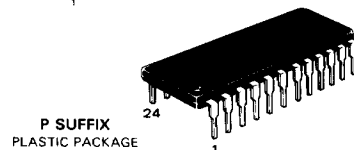
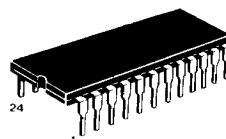
- Fully Static Operation
- Three-State Data Output
- Mask-Programmable Chip Selects for Simplified Memory Expansion
- Single  $\pm 10\%$  5-Volt Power Supply
- TTL Compatible
- Maximum Access Time = 350 ns
- Plug-in Compatible with 2316E
- Pin Compatible with 2708 and TMS2716 EPROMs

**MOS**

(N-CHANNEL, SILICON-GATE)

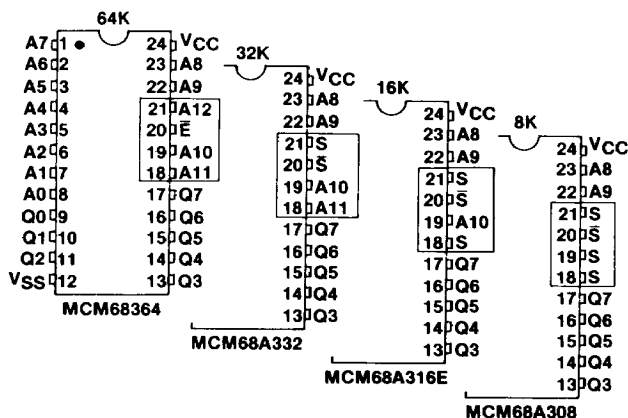
**2048 X 8 BIT  
READ ONLY MEMORY**

C SUFFIX  
FRIT-SEAL CERAMIC PACKAGE  
CASE 623



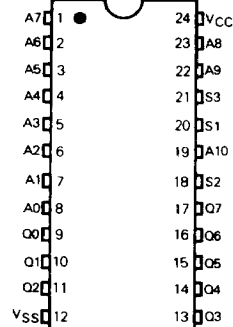
P SUFFIX  
PLASTIC PACKAGE  
CASE 709

### MOTOROLA'S PIN-COMPATIBLE ROM FAMILY



INDUSTRY STANDARD PINOUTS

### PIN ASSIGNMENT



### PIN NAMES

A0 - A10	Address Inputs
S1 - S3	Chip Selects
Q0 - Q7	Data Output
VCC	+5 V Power Supply
VSS	Ground

ROM

DC OPERATING CONDITIONS AND CHARACTERISTICS  
(Full operating voltage and temperature range unless otherwise noted)

RECOMMENDED DC OPERATING CONDITIONS

Parameter	Symbol	Min	Typ	Max	Unit
Supply Voltage	V <sub>CC</sub>	4.5	5.0	5.5	V <sub>dC</sub>
Input High Voltage	V <sub>IH</sub>	2.0	—	5.5	V <sub>dC</sub>
Input Low Voltage	V <sub>IL</sub>	−0.3	—	0.8	V <sub>dC</sub>

DC CHARACTERISTICS

Characteristic	Symbol	Min	Max	Unit
Input Current (V <sub>in</sub> = 0 to 5.5 V)	I <sub>in</sub>	−2.5	2.5	μA <sub>dC</sub>
Output High Voltage (I <sub>OH</sub> = −205 μA)	V <sub>OH</sub>	2.4	—	V <sub>dC</sub>
Output Low Voltage (I <sub>OL</sub> = 1.6 mA)	V <sub>OL</sub>	—	0.4	V <sub>dC</sub>
Output Leakage Current (Three-State) (S = 0.8 V or $\bar{S}$ = 2.0 V, V <sub>out</sub> = 0.4 V to 2.4 V)	I <sub>LO</sub>	−10	10	μA <sub>dC</sub>
Supply Current (V <sub>CC</sub> = 5.5 V, T <sub>A</sub> = 0°C)	I <sub>CC</sub>	—	130	mA <sub>dC</sub>

ABSOLUTE MAXIMUM RATINGS (See Note 1)

Rating	Symbol	Value	Unit
Supply Voltage	V <sub>CC</sub>	−0.3 to +7.0	V <sub>dC</sub>
Input Voltage	V <sub>in</sub>	−0.3 to +7.0	V <sub>dC</sub>
Operating Temperature Range	T <sub>A</sub>	0 to +70	°C
Storage Temperature Range	T <sub>stg</sub>	−65 to +150	°C

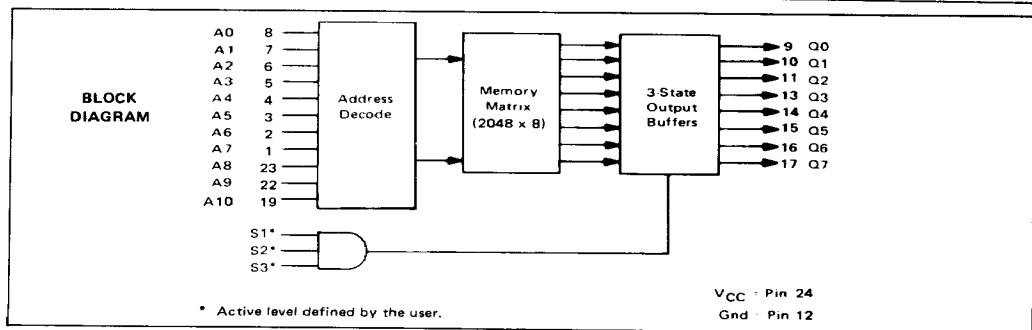
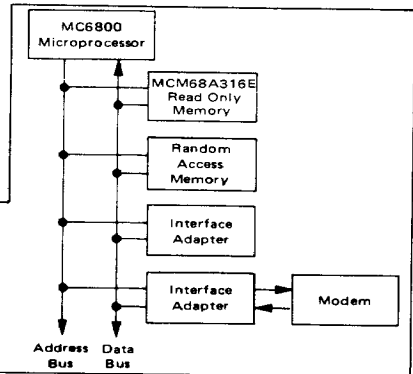
NOTE 1: Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to RECOMMENDED OPERATING CONDITIONS. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.

CAPACITANCE

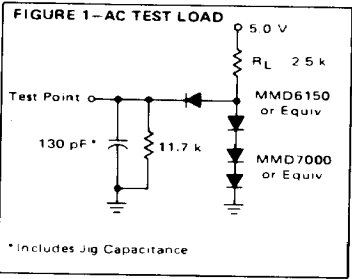
(f = 2.0 MHz, T<sub>A</sub> = 25°C, periodically sampled rather than 100% tested)

Characteristic	Symbol	Max	Unit
Input Capacitance	C <sub>in</sub>	7.5	pF
Output Capacitance	C <sub>out</sub>	12.5	pF

M6800 MICROCOMPUTER FAMILY  
BLOCK DIAGRAM



MCM68A316E

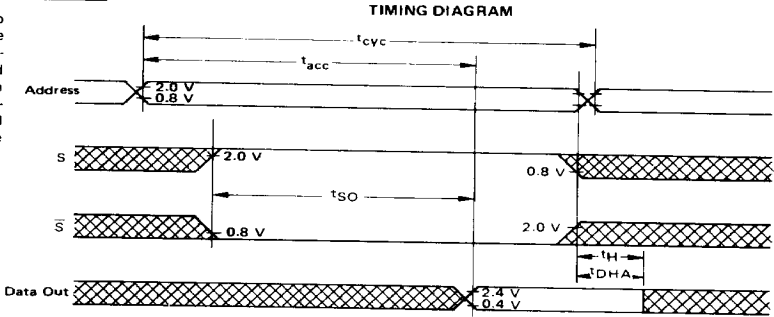


This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit.

**AC OPERATING CONDITIONS AND CHARACTERISTICS**

(Full operating voltage and temperature unless otherwise noted.  
All timing with  $t_r = t_f = 20$  ns, Load of Figure 1)

Characteristic	Symbol	Min	Max	Unit
Cycle Time	$t_{cyc}$	350	—	ns
Access Time	$t_{acc}$	—	350	ns
Chip Select to Output Delay	$t_{SO}$	—	150	ns
Data Hold from Address	$t_{DHA}$	10	—	ns
Data Hold from Deselection	$t_H$	10	150	ns



ROM

## CUSTOM PROGRAMMING

By the programming of a single photomask for the MCM68A316E, the customer may specify the content of the memory and the method of enabling the outputs.

Information on the general options of the MCM68A316E should be submitted on an Organizational Data form such as that shown in Figure 2. ("No-Connect" must always be the highest order Chip Select(s).)

Information for custom memory content may be sent to Motorola in one of two forms (shown in order of preference):

1. EPROM (TMS2716 or MCM2716)
2. Magnetic Tape  
9 track, 800 bpi, odd parity written in EBCDIC character code. Motorola's R.O.M.S. format.

FIGURE 2 — FORMAT FOR PROGRAMMING GENERAL OPTIONS

ORGANIZATIONAL DATA MCM68A316E MOS READ ONLY MEMORY			
<div style="display: flex; justify-content: space-between;"> <div style="width: 60%;"> <p>Customer:</p> <p>Company _____</p> <p>Part No. _____</p> <p>Originator _____</p> <p>Phone No. _____</p> </div> <div style="width: 35%; border: 1px solid black; padding: 5px;"> <p style="text-align: center;">Motorola Use Only:</p> <p>Quote: _____</p> <p>Part No.: _____</p> <p>Specif. No.: _____</p> </div> </div>			
<p>Chip Select:</p>	<p>Active High</p>	<p>Active Low</p>	<p>No Connect</p>
S1	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
S2	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
S3	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>